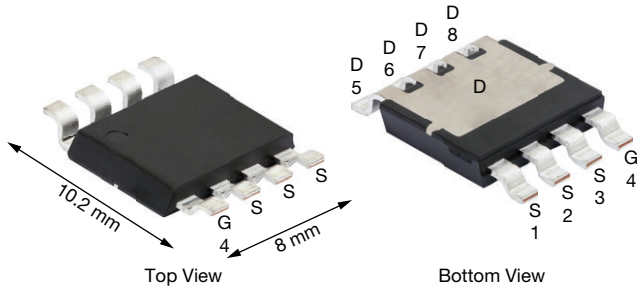
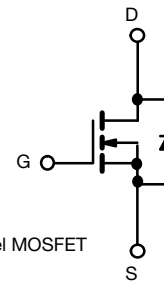


Automotive N-Channel 100 V (D-S) 175 °C MOSFET

PowerPAK® 8 x 8LR

FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Thin 1.9 mm height
- Material categorization:
for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE


RoHS
COMPLIANT
HALOGEN
FREE


N-Channel MOSFET

| PRODUCT SUMMARY | |
|---|---------|
| V _{DS} (V) | 100 |
| R _{DS(on)} (Ω) at V _{GS} = 10 V | 0.00253 |
| I _D (A) | 296 |
| Configuration | Single |

| ORDERING INFORMATION | |
|---------------------------------|---|
| Package | PowerPAK 8 x 8LR |
| Lead (Pb)-free and halogen-free | SQJQ112ER (for detailed order number please see www.vishay.com/doc?79776) |

| ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted) | | | | |
|---|-------------------------|-----------------------------------|-------------|------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Drain-source voltage | | V _{DS} | 100 | V |
| Gate-source voltage | | V _{GS} | ± 20 | |
| Continuous drain current | T _C = 25 °C | I _D | 296 | A |
| | T _C = 125 °C | | 171 | |
| Continuous source current (diode conduction) | | I _S | 545 | |
| Pulsed drain current ^a | | I _{DM} | 655 | |
| Single pulse avalanche current | L = 0.1 mH | I _{AS} | 69 | |
| Single pulse avalanche energy | | E _{AS} | 242 | |
| Maximum power dissipation | T _C = 25 °C | P _D | 600 | W |
| | T _C = 125 °C | | 200 | |
| Operating junction and storage temperature range | | T _J , T _{stg} | -55 to +175 | °C |
| Soldering recommendations (peak temperature) ^c | | | 260 | |

| THERMAL RESISTANCE RATINGS | | | | |
|----------------------------|------------------------|-------------------|-------|------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Junction-to-ambient | PCB mount ^b | R _{thJA} | 40 | °C/W |
| Junction-to-case (drain) | | R _{thJC} | 0.25 | |

Notes

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257)



| SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | | |
|--|---------------|---|--|------|--------|-----------|---------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | | |
| Drain-source breakdown voltage | V_{DS} | $V_{GS} = 0, I_D = 250\text{ }\mu\text{A}$ | | 100 | - | - | V |
| Gate-source threshold voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | | 2 | 3 | 3.5 | |
| Gate-source leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | - | - | ± 100 | nA |
| Zero gate voltage drain current | I_{DSS} | $V_{GS} = 0\text{ V}$ | $V_{DS} = 100\text{ V}$ | - | - | 1 | μA |
| | | $V_{GS} = 0\text{ V}$ | $V_{DS} = 100\text{ V}, T_J = 125\text{ }^\circ\text{C}$ | - | - | 50 | |
| | | $V_{GS} = 0\text{ V}$ | $V_{DS} = 100\text{ V}, T_J = 175\text{ }^\circ\text{C}$ | - | - | 500 | |
| On-state drain current ^a | $I_{D(on)}$ | $V_{GS} = 10\text{ V}$ | $V_{DS} \geq 5\text{ V}$ | 50 | - | - | A |
| Drain-source on-state resistance ^a | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$ | $I_D = 20\text{ A}$ | - | 0.0021 | 0.00253 | Ω |
| | | $V_{GS} = 10\text{ V}$ | $I_D = 20\text{ A}, T_J = 125\text{ }^\circ\text{C}$ | - | - | 0.0054 | |
| | | $V_{GS} = 10\text{ V}$ | $I_D = 20\text{ A}, T_J = 175\text{ }^\circ\text{C}$ | - | - | 0.0068 | |
| Forward transconductance ^b | g_{fs} | $V_{DS} = 15\text{ V}, I_D = 15\text{ A}$ | | - | 45 | - | S |
| Dynamic ^b | | | | | | | |
| Input capacitance | C_{iss} | $V_{GS} = 0\text{ V}$ | $V_{DS} = 25\text{ V}, f = 1\text{ MHz}$ | - | 11388 | 15 945 | μF |
| Output capacitance | C_{oss} | | | - | 1326 | 1857 | |
| Reverse transfer capacitance | C_{rss} | | | - | 80 | 112 | |
| Total gate charge ^c | Q_g | $V_{GS} = 10\text{ V}$ | $V_{DS} = 50\text{ V}, I_D = 20\text{ A}$ | - | 181 | 272 | nC |
| Gate-source charge ^c | Q_{gs} | | | - | 48 | - | |
| Gate-drain charge ^c | Q_{gd} | | | - | 37 | - | |
| Gate resistance | R_g | f = 1 MHz | | 0.7 | 1.5 | 2.3 | Ω |
| Turn-on delay time ^c | $t_{d(on)}$ | $V_{DD} = 50\text{ V}, R_L = 2.5\text{ }\Omega,$ $I_D \cong 20\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$ | | - | 21 | 30 | ns |
| Rise time ^c | t_r | | | - | 16 | 24 | |
| Turn-off delay time ^c | $t_{d(off)}$ | | | - | 67 | 95 | |
| Fall time ^c | t_f | | | - | 16 | 24 | |
| Source-Drain Diode Ratings and Characteristics ^b | | | | | | | |
| Pulsed current ^a | I_{SM} | | | - | - | 655 | A |
| Forward voltage | V_{SD} | $I_F = 40\text{ A}, V_{GS} = 0\text{ V}$ | | - | 0.7 | 1.2 | V |
| Body diode reverse recovery time | t_{rr} | $I_F = 15\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ | | - | 70 | 140 | ns |
| Body diode reverse recovery charge | Q_{rr} | | | - | 172 | 344 | nC |
| Reverse recovery fall time | t_a | | | - | 44 | - | ns |
| Reverse recovery rise time | t_b | | | - | 26 | - | |
| Body diode peak reverse recovery current | $I_{RM(REC)}$ | | | | | - | 4.3 |

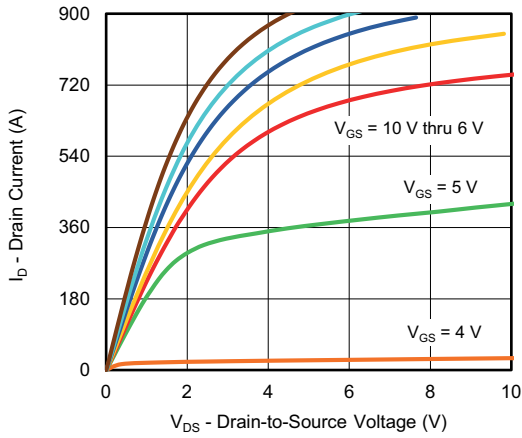
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

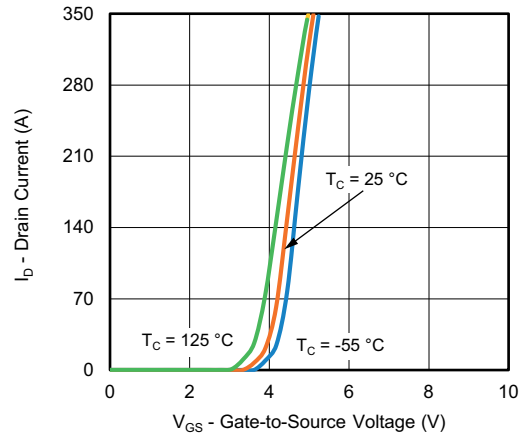
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



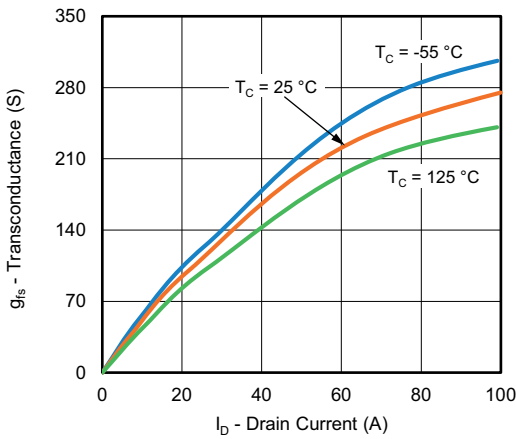
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



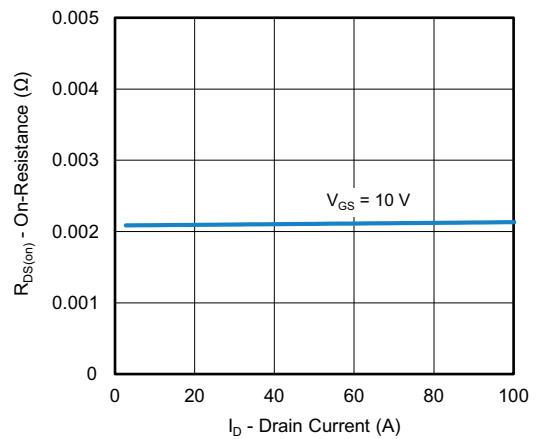
Output Characteristics



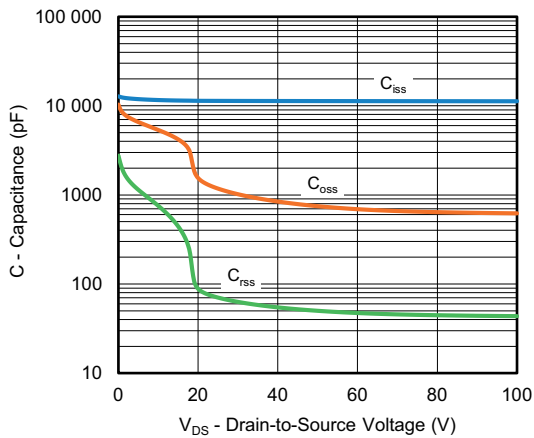
Transfer Characteristics



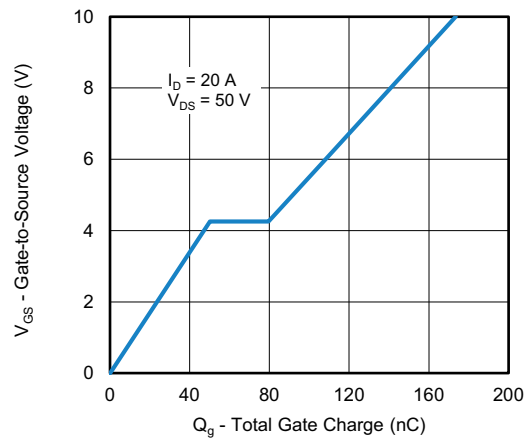
Transconductance



On-Resistance vs. Drain Current



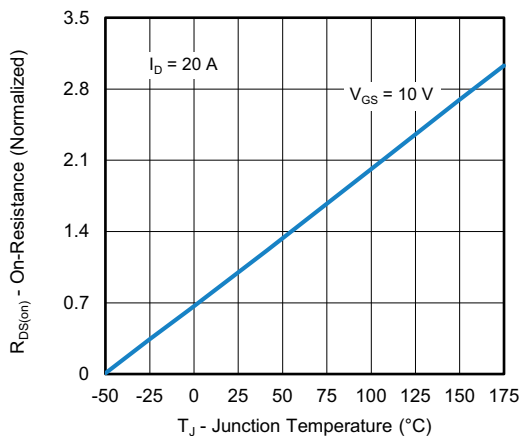
Capacitance



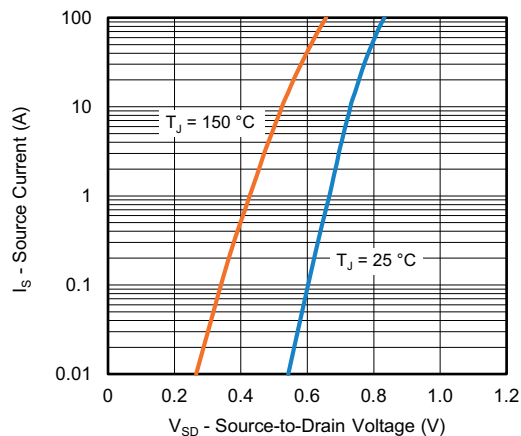
Gate Charge



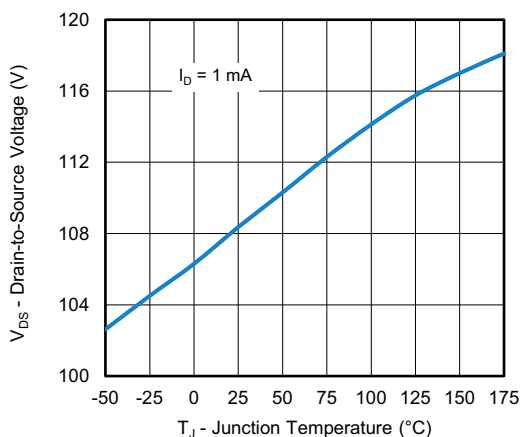
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



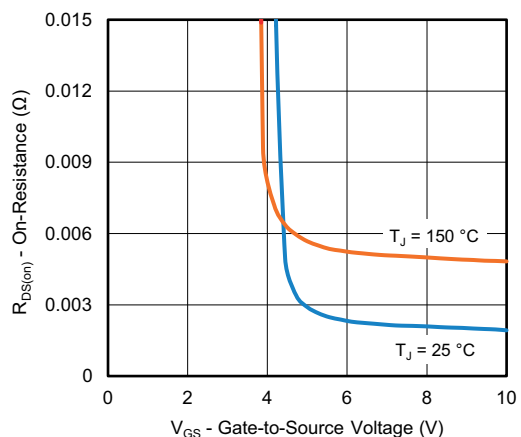
On-Resistance vs. Junction Temperature



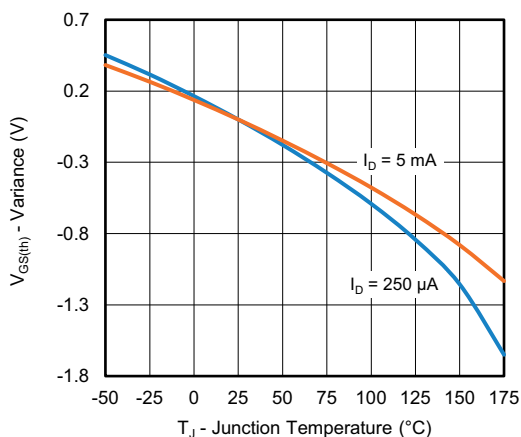
Source Drain Diode Forward Voltage



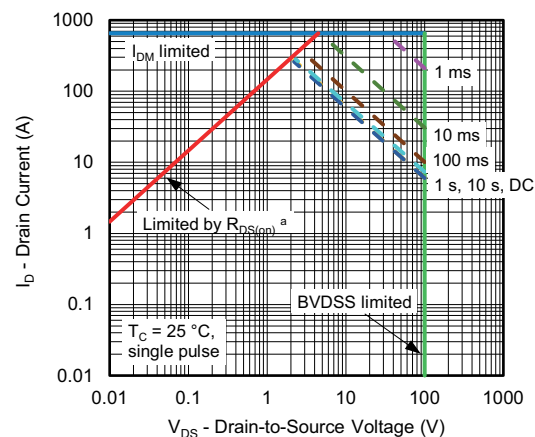
Drain Source Breakdown vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



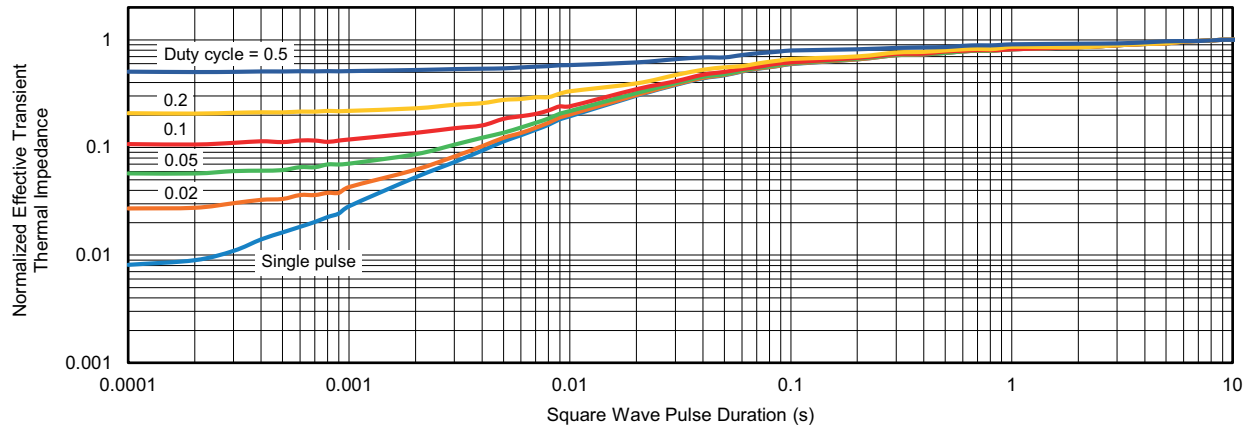
Safe Operating Area

Note

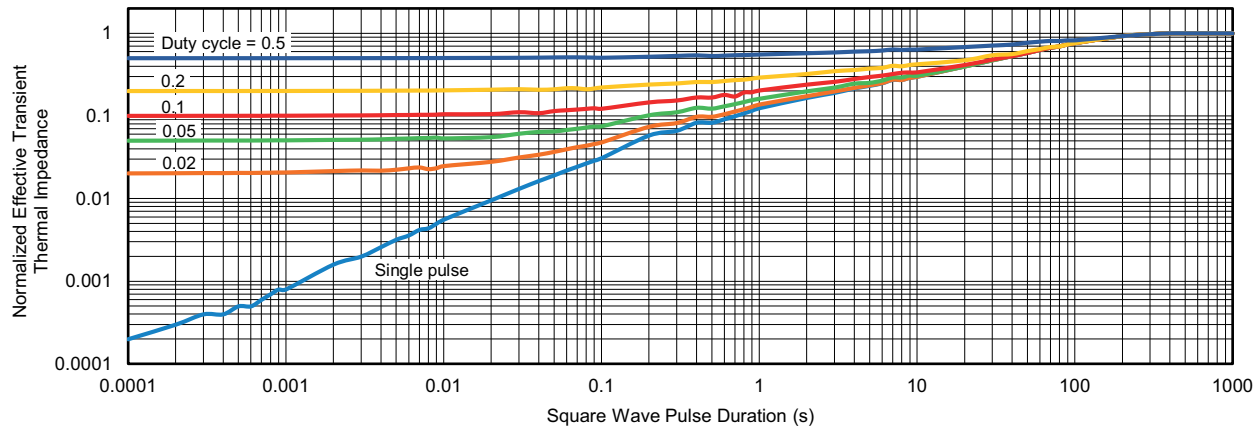
- a. V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient

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